

74LVC823A

9-bit D-type flip-flop with 5 V tolerant inputs/outputs; positive edge-trigger; 3-state

Rev. 4 — 8 April 2013

Product data sheet

1. General description

The 74LVC823A is a 9-bit D-type flip-flop with common clock (pin CP), clock enable (pin \overline{CE}), master reset (pin \overline{MR}) and 3-state outputs (pins Qn) for bus-oriented applications. The 9 flip-flops stores the state of their individual D-inputs that meet the set-up and hold times requirements on the LOW to HIGH CP transition, provided pin \overline{CE} is LOW. When pin \overline{CE} is HIGH, the flip-flops hold their data. A LOW on pin \overline{MR} resets all flip-flops. When pin \overline{OE} is LOW, the contents of the 9 flip-flops are available at the outputs. When pin \overline{OE} is HIGH, the outputs go to the high-impedance OFF-state. Operation of the \overline{OE} input does not affect the state of the flip-flops.

Inputs can be driven from either 3.3 V or 5 V devices. When disabled, up to 5.5 V can be applied to the outputs. These features allow the use of these devices as translators in mixed 3.3 V and 5 V applications.

2. Features and benefits

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Flow-through pinout architecture
- 9-bit positive edge-triggered register
- Independent register and 3-state buffer operation
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A (2.3 V to 2.7 V)
 - ◆ JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-B exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$.



3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC823AD	-40 °C to +125 °C	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1
74LVC823ADB	-40 °C to +125 °C	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm	SOT340-1
74LVC823APW	-40 °C to +125 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1
74LVC823ABQ	-40 °C to +125 °C	DHVQFN24	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 × 5.5 × 0.85 mm	SOT815-1

4. Functional diagram

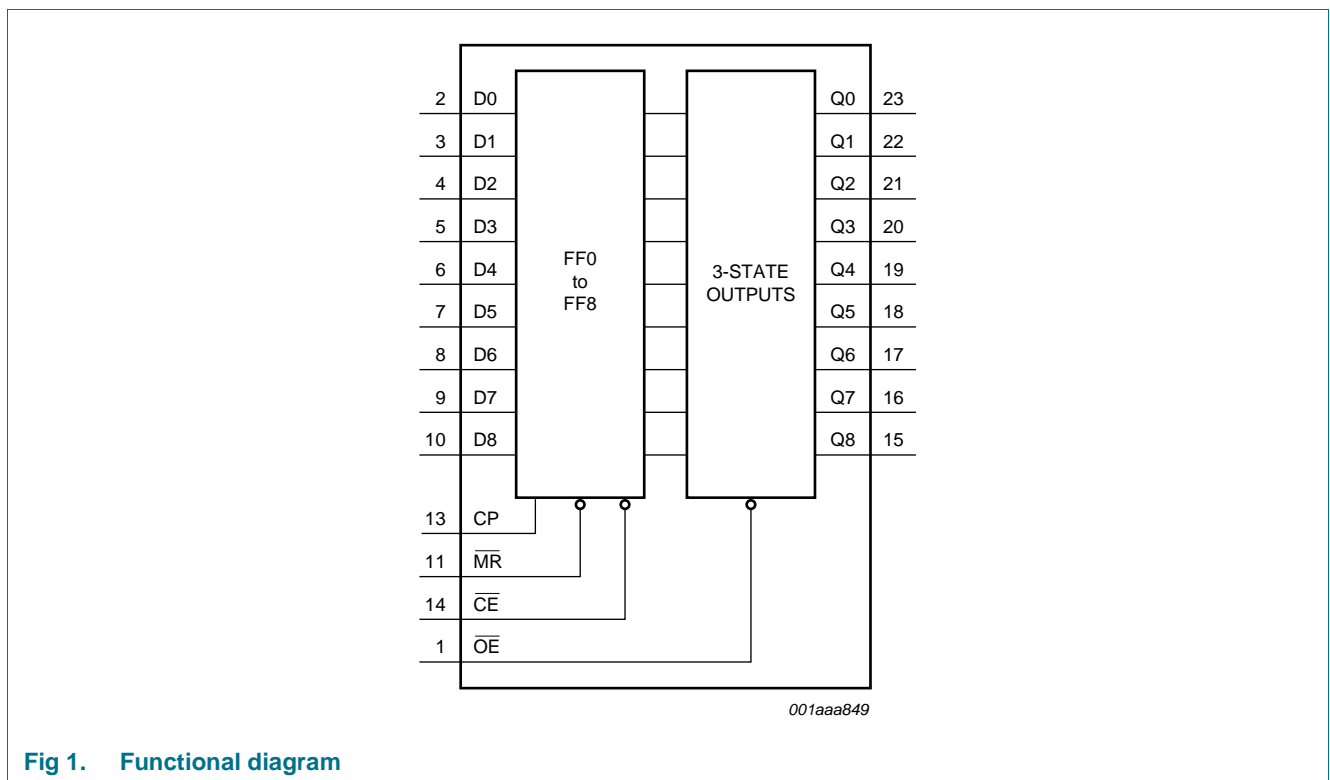


Fig 1. Functional diagram

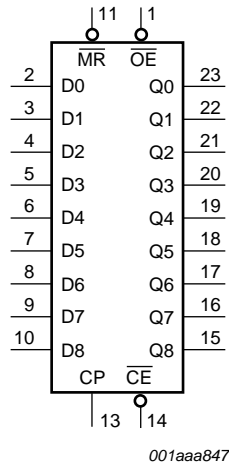


Fig 2. Logic symbol

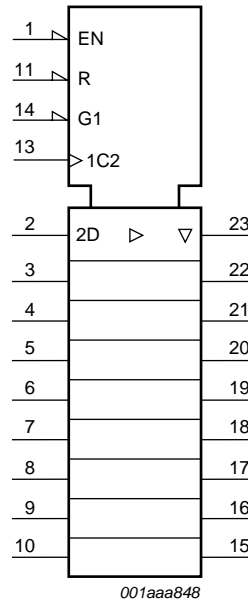


Fig 3. IEC logic symbol

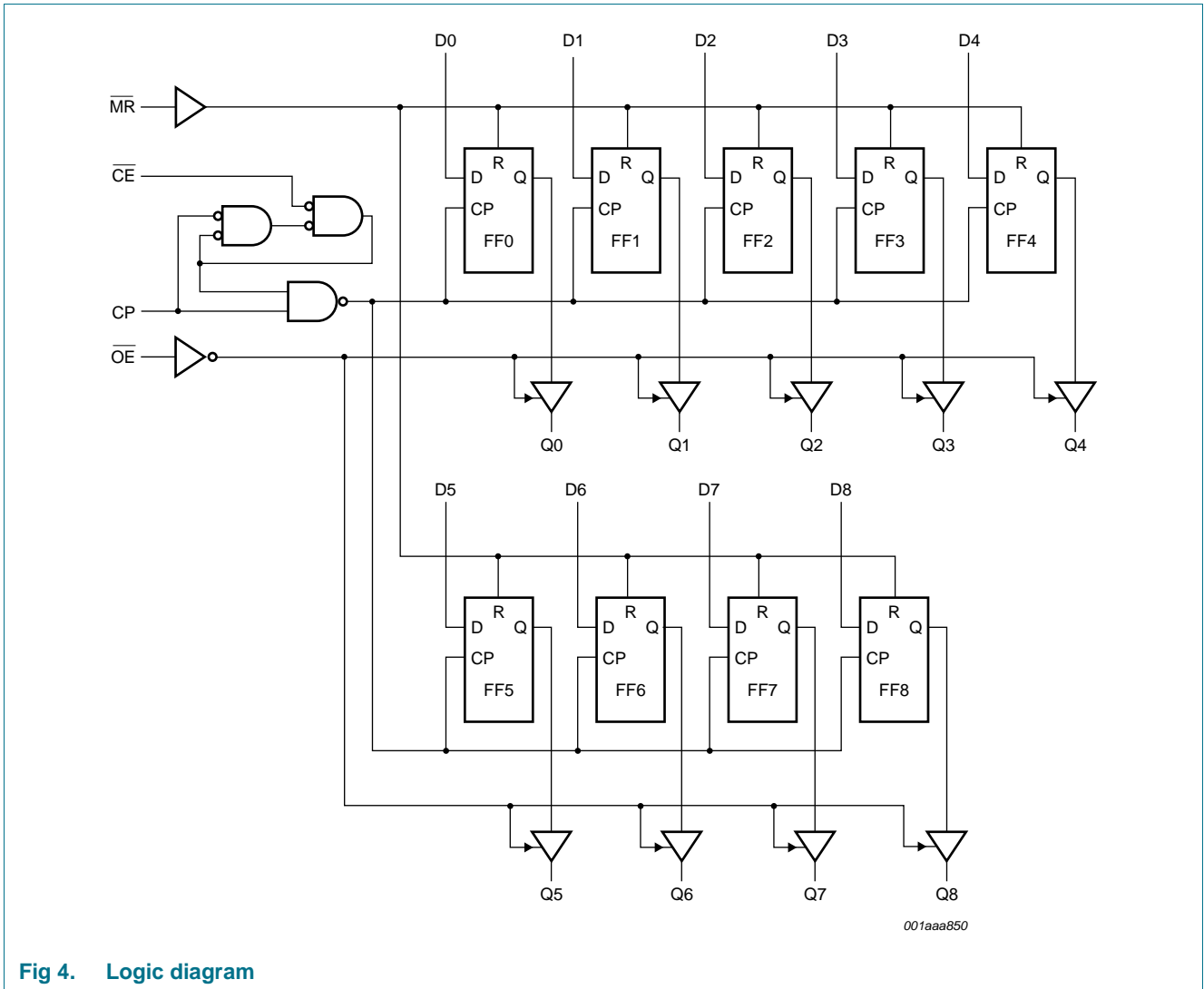
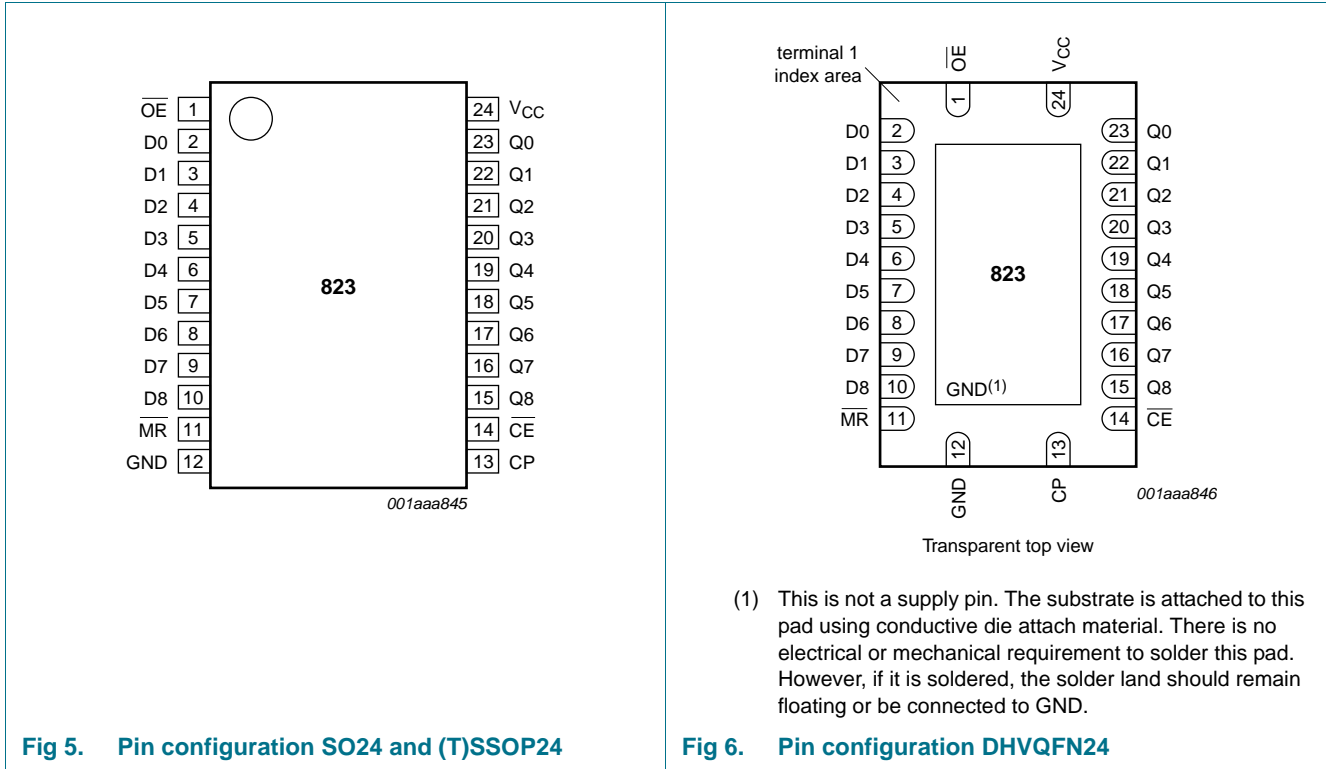


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Pin	Name	Description
OE	1	output enable input (active LOW)
MR	11	master reset input (active LOW)
D[0:8]	2, 3, 4, 5, 6, 7, 8, 9, 10	data input
Q[0:8]	23, 22, 21, 20, 19, 18, 17, 16, 15	3-state flip-flop output
CP	13	clock input (LOW to HIGH; edge-triggered)
CE	14	clock enable input (active LOW)
GND	12	ground (0 V)
V _{CC}	24	supply voltage

6. Functional description

Table 3. Function table [1]

Operating mode	Input					Internal flip-flop	Output Qn
	OE	MR	CE	CP	Dn		
Clear	L	L	X	X	X	L	L
Load and read register	L	H	L	↑	l	L	L
	L	H	L	↑	h	H	H
Load register and disable outputs	H	H	L	↑	l	L	Z
	H	H	L	↑	h	H	Z
Hold	L	H	H	NC	X	NC	NC

- [1] H = HIGH voltage level
 h = HIGH voltage level one set-up time prior to the LOW to HIGH CP transition
 L = LOW voltage level
 l = LOW voltage level one set-up time prior to the LOW to HIGH CP transition
 Z = high-impedance OFF-state
 ↑ = LOW to HIGH level transition
 X = don't care
 NC = no change

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_O	output voltage	HIGH or LOW state	[2] -0.5	$V_{CC} + 0.5$	V
		3-state	[2] -0.5	+6.5	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	500	mW

- [1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.
 [2] The output voltage ratings may be exceeded if the output current ratings are observed.
 [3] For SO24 packages: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For SSOP24 and TSSOP24 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN24 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	HIGH or LOW state	0	-	V _{CC}	V
		3-state	0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
		V _{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	0.65 × V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = -100 μA; V _{CC} = 1.65 V to 3.6 V	V _{CC} - 0.2	-	-	V _{CC} - 0.3	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I _O = -18 mA; V _{CC} = 3.0 V	2.4	-	-	2.25	-	V
V _{OL}	LOW-level output voltage	I _O = -24 mA; V _{CC} = 3.0 V	2.2	-	-	2.0	-	V
		V _I = V _{IH} or V _{IL}						
		I _O = 100 μA; V _{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	-	0.6	V
I _I	input leakage current	I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	-	0.8	V
		V _{CC} = 3.6 V; V _I = 5.5 V or GND	-	±0.1	±5	-	±20	μA

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 3.6 V; V _O = 5.5 V or GND;	-	0.1	±5	-	±20	µA
I _{OFF}	power-off leakage current	V _{CC} = 0 V; V _I or V _O = 5.5 V	-	0.1	±10	-	±20	µA
I _{CC}	supply current	V _{CC} = 3.6 V; V _I = V _{CC} or GND; I _O = 0 A	-	0.1	10	-	40	µA
ΔI _{CC}	additional supply current	per input pin; V _{CC} = 2.7 V to 3.6 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	-	5	500	-	5000	µA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND to V _{CC}	-	5.0	-	-	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	CP to Qn; see Figure 7 ^[2]						
		V _{CC} = 1.2 V	-	20	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	2.4	8.4	18.7	2.4	21.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	4.4	9.6	1.7	11.1	ns
		V _{CC} = 2.7 V	1.5	4.1	8.9	1.5	11.5	ns
t _{PHL}	HIGH to LOW propagation delay	MR to Qn; see Figure 9						
		V _{CC} = 1.2 V	-	15	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	9.5	21.4	2.1	24.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	4.9	10.5	1.5	12.1	ns
		V _{CC} = 2.7 V	1.5	4.7	8.8	1.5	11.0	ns
t _{en}	enable time	OE to Qn; see Figure 10 ^[2]						
		V _{CC} = 1.2 V	-	18	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	7.4	16.5	1.7	19.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	4.2	9.1	1.5	10.5	ns
		V _{CC} = 2.7 V	1.5	4.3	8.3	1.5	10.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	3.4	7.2	1.5	9.0	ns

Table 7. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{dis}	disable time	$\overline{\text{OE}}$ to Qn; see Figure 10 ^[2]						
		V _{CC} = 1.2 V	-	8.0	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.2	10.0	2.3	11.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.3	5.6	1.0	6.5	ns
		V _{CC} = 2.7 V	1.5	3.2	7.1	1.5	9.0	ns
t _w	pulse width	clock HIGH or LOW; see Figure 7						
		V _{CC} = 1.65 V to 1.95 V	5.0	-	-	5.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	4.0	-	-	4.0	-	ns
		V _{CC} = 2.7 V	3.3	-	-	3.3	-	ns
		V _{CC} = 3.0 V to 3.6 V	3.3	1.7	-	3.3	-	ns
		master reset HIGH or LOW; see Figure 9						
		V _{CC} = 1.65 V to 1.95 V	5.0	-	-	5.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	4.0	-	-	4.0	-	ns
		V _{CC} = 2.7 V	3.3	-	-	3.3	-	ns
		V _{CC} = 3.0 V to 3.6 V	3.3	1.7	-	3.3	-	ns
t _{su}	set-up time	Dn to CP; see Figure 8						
		V _{CC} = 1.65 V to 1.95 V	3.0	-	-	3.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	-	-	2.0	-	ns
		V _{CC} = 2.7 V	1.0	-	-	1.0	-	ns
		V _{CC} = 3.0 V to 3.6 V	+1.8	-0.8	-	+1.8	-	ns
		$\overline{\text{CE}}$ to CP; see Figure 8						
		V _{CC} = 1.65 V to 1.95 V	3.0	-	-	3.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	-	-	2.0	-	ns
		V _{CC} = 2.7 V	1.8	-	-	1.8	-	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	0.0	-	1.3	-	ns
t _{rec}	recovery time	MR; see Figure 9						
		V _{CC} = 1.65 V to 1.95 V	3.0	-	-	3.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	2.5	-	-	2.5	-	ns
		V _{CC} = 2.7 V	2.0	-	-	2.0	-	ns
		V _{CC} = 3.0 V to 3.6 V	+1.0	-0.5	-	+1.0	-	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			-40 °C to +125 °C		Unit		
			Min	Typ ^[1]	Max	Min	Max			
t _h	hold time	Dn to CP; see Figure 8								
		V _{CC} = 1.65 V to 1.95 V	3.0	-	-	3.0	-	ns		
		V _{CC} = 2.3 V to 2.7 V	2.5	-	-	2.5	-	ns		
		V _{CC} = 2.7 V	2.0	-	-	2.0	-	ns		
		V _{CC} = 3.0 V to 3.6 V	2.0	0.8	-	2.0	-	ns		
		$\overline{\text{CE}}$ to CP; see Figure 8								
		V _{CC} = 1.65 V to 1.95 V	3.0	-	-	3.0	-	ns		
		V _{CC} = 2.3 V to 2.7 V	2.0	-	-	2.0	-	ns		
f _{max}	maximum frequency	see Figure 7								
		V _{CC} = 1.65 V to 1.95 V	100	-	-	80	-	MHz		
		V _{CC} = 2.3 V to 2.7 V	125	-	-	100	-	MHz		
		V _{CC} = 2.7 V	150	-	-	120	-	MHz		
t _{sk(o)}	output skew time	V _{CC} = 3.0 V to 3.6 V	^[3]	-	-	1.0	-	1.5	ns	
		C _{PD}	power dissipation capacitance	per input; V _I = GND to V _{CC}	^[4]					
				V _{CC} = 1.65 V to 1.95 V	-	12.4	-	-	-	pF
				V _{CC} = 2.3 V to 2.7 V	-	14.5	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	16.4	-	-	-	pF		

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V and 3.3 V respectively.

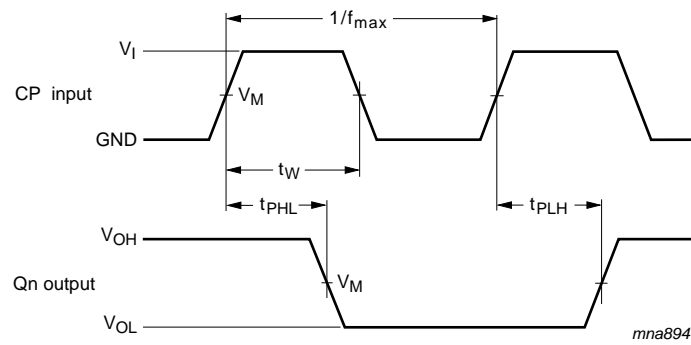
[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 t_{en} is the same as t_{PZL} and t_{PZH}.
 t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

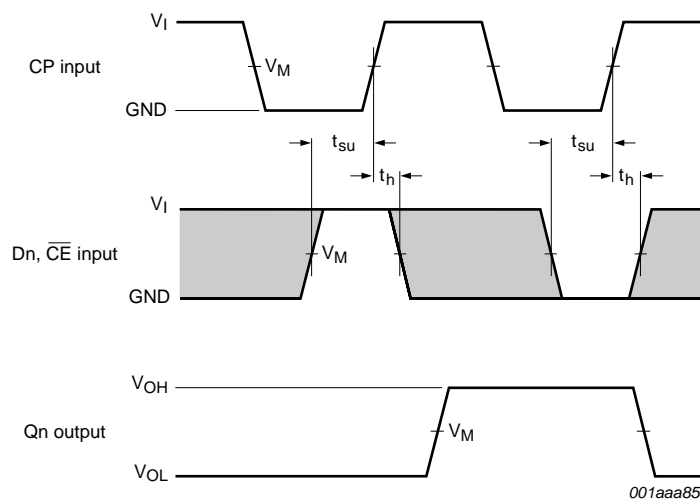
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$$
 where:
 f_i = input frequency in MHz; f_o = output frequency in MHz
 C_L = output load capacitance in pF
 V_{CC} = supply voltage in Volts
 N = number of inputs switching
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs

11. Waveforms



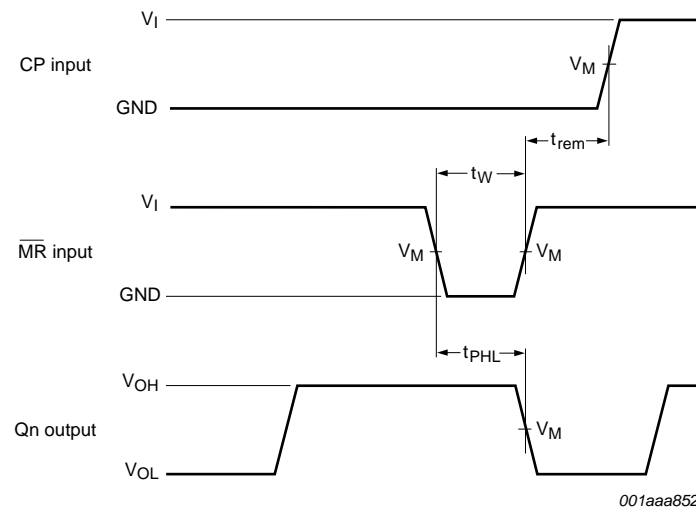
Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig 7. Clock to output propagation delays, clock pulse width, and maximum frequency



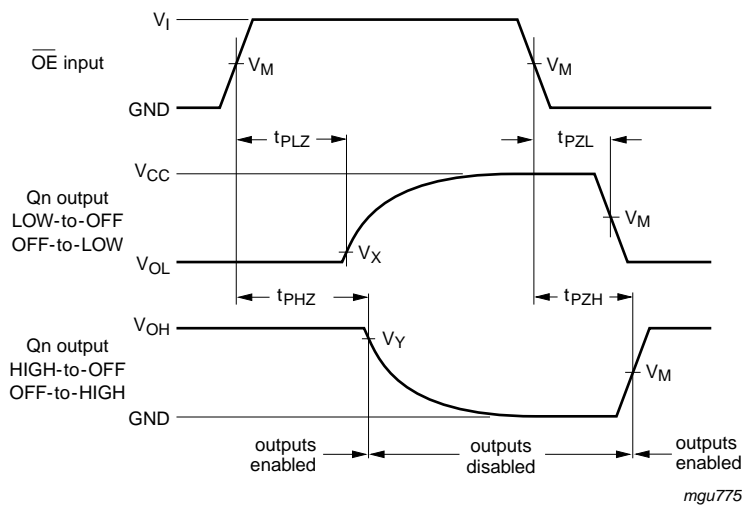
Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.
 The shaded areas indicate when the input is permitted to change for predicable output performance.

Fig 8. Data set-up and hold times for data and clock enable inputs to clock input



Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig 9. Master reset pulse width, master reset to clock removal time and master reset to output propagation delay

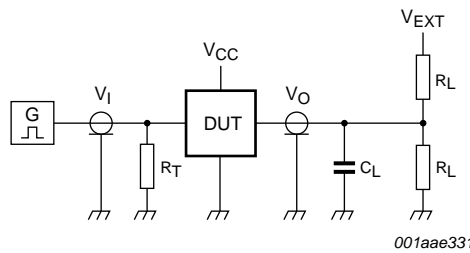
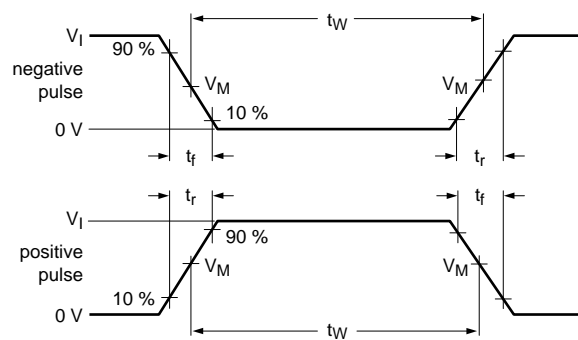


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are the typical output voltage drops that occur with the output load.

Fig 10. 3-state outputs enable and disable times

Table 8. Measurement points

Supply voltage	Input		Output		
V _{CC}	V _I	V _M	V _M	V _X	V _Y
1.2 V	V _{CC}	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
1.65 V to 1.95 V	V _{CC}	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
2.3 V to 2.7 V	V _{CC}	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
2.7 V	2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} - 0.3 V
3.0 V to 3.6 V	2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} - 0.3 V



001aae331

Test data is given in [Table 9](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 11. Load circuitry for switching times

Table 9. Test data

Supply voltage	Input		Load		V _{EXT}		
	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V _{CC}	GND
1.65 V to 1.95 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V _{CC}	GND
2.3 V to 2.7 V	V _{CC}	≤ 2 ns	30 pF	500 Ω	open	2 × V _{CC}	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V _{CC}	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V _{CC}	GND

12. Package outline

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1

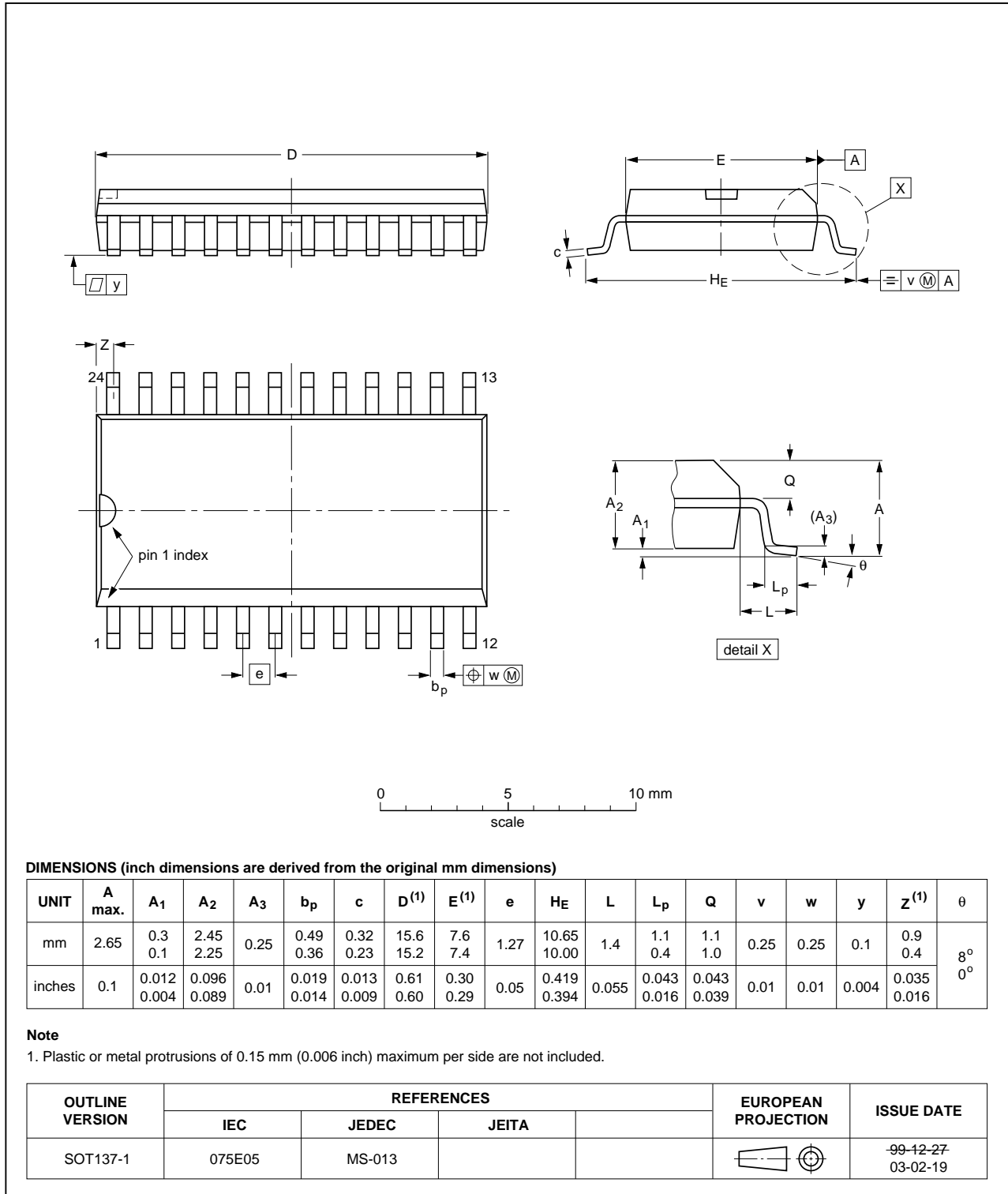


Fig 12. Package outline SOT137-1 (SO24)

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm

SOT340-1

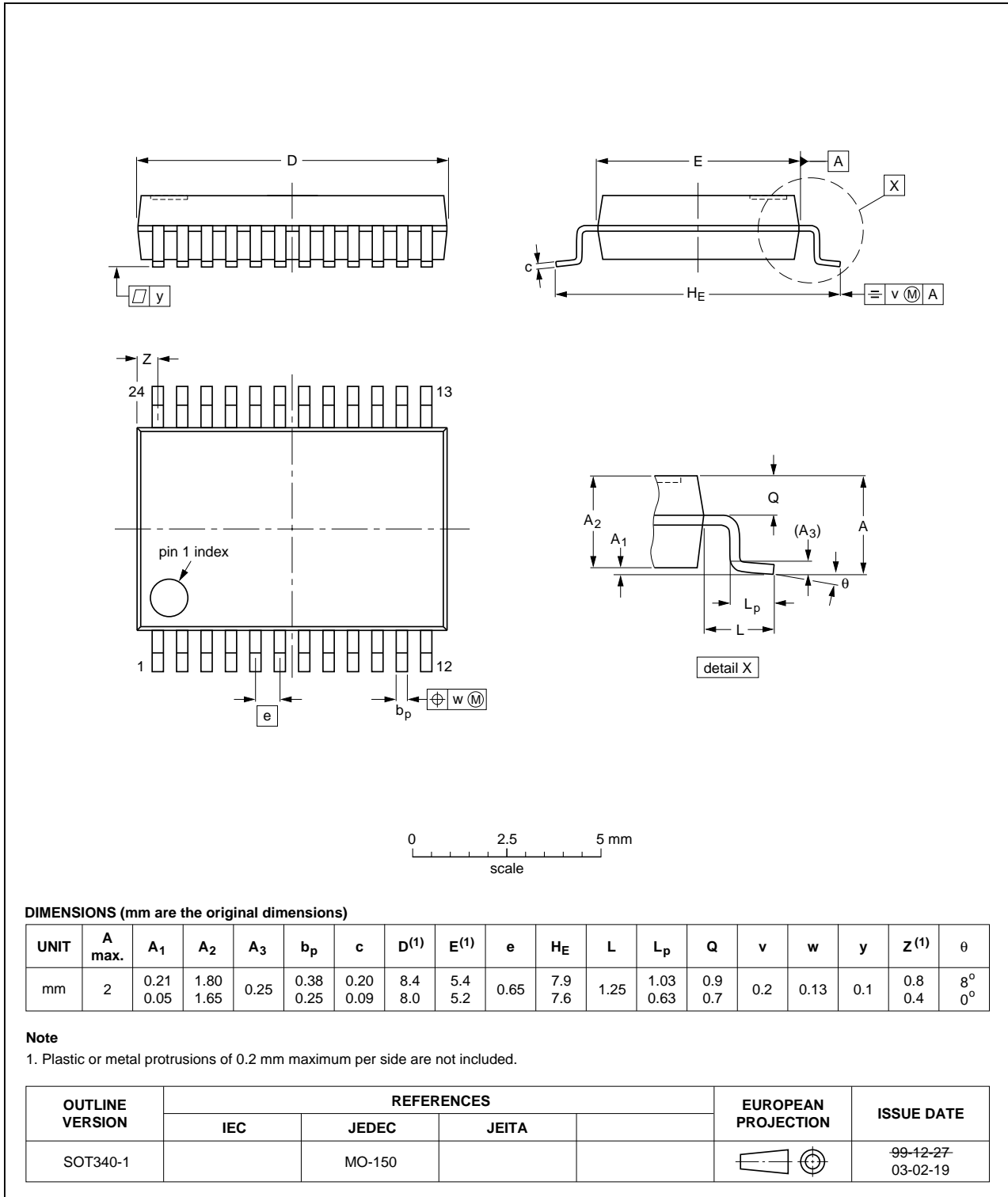


Fig 13. Package outline SOT340-1 (SSOP24)

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1

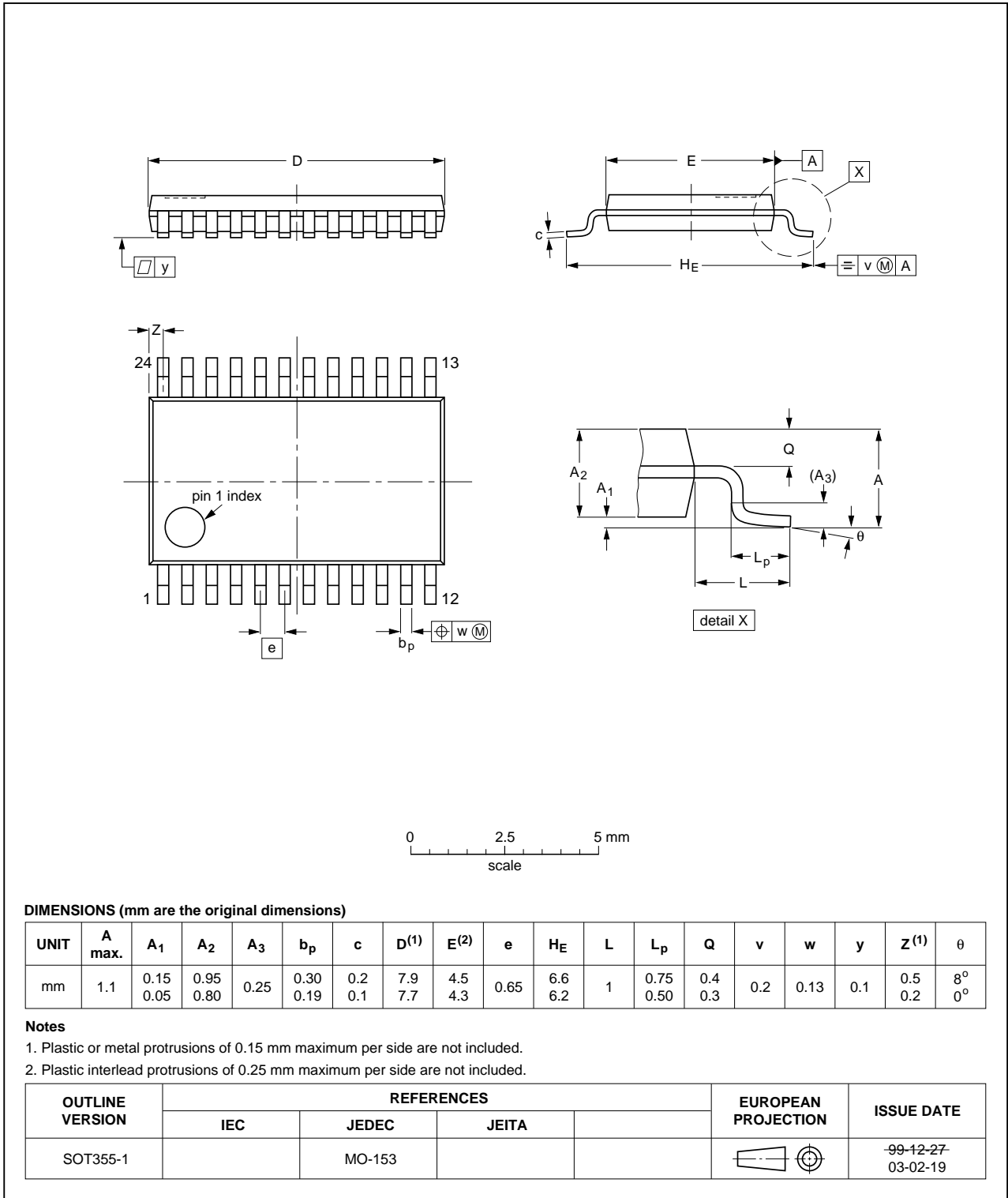


Fig 14. Package outline SOT355-1 (TSSOP24)

DHVQFN24: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 x 5.5 x 0.85 mm

SOT815-1

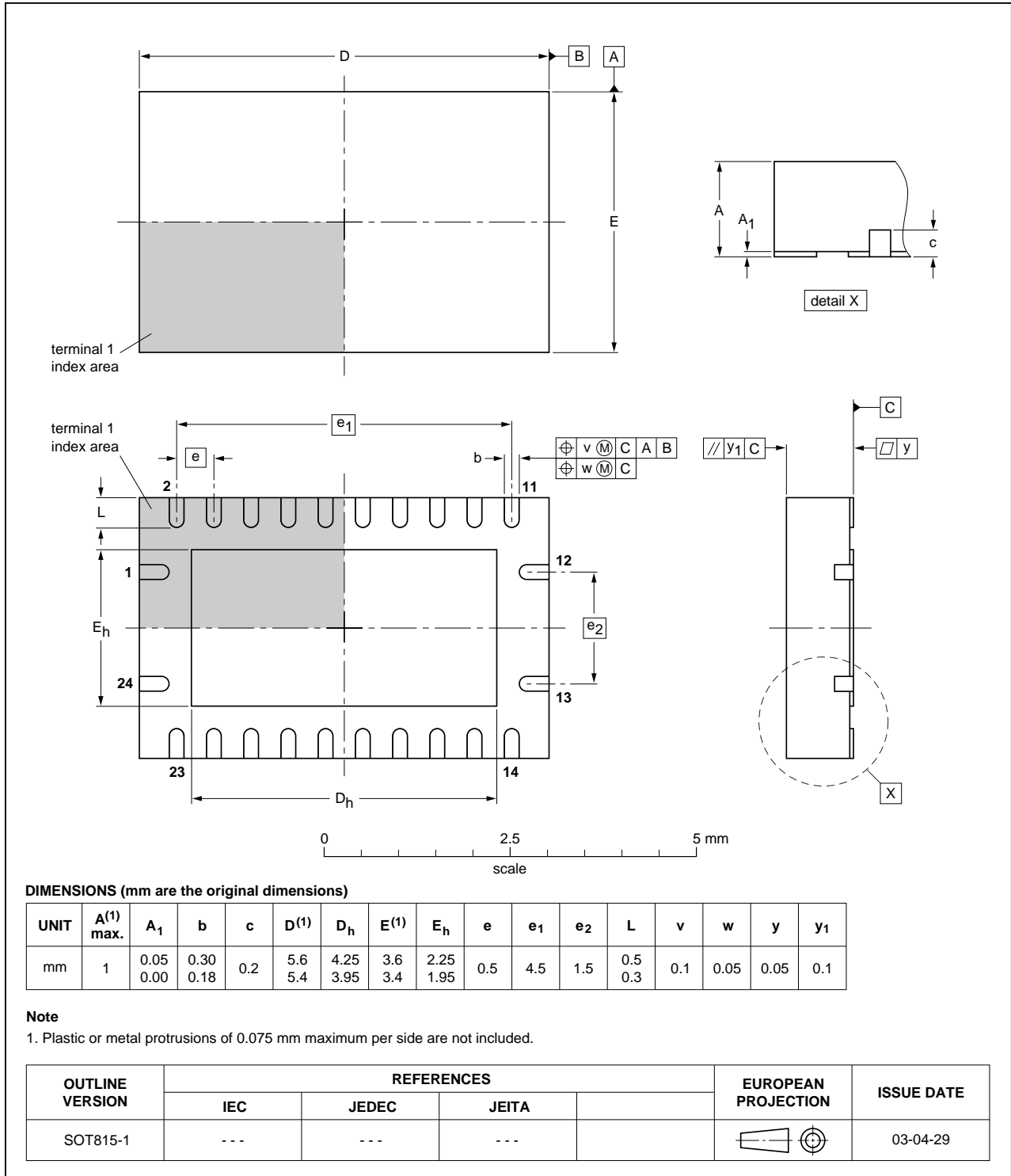


Fig 15. Package outline SOT815-1 (DHVQFN24)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC823A v.4	20130408	Product data sheet	-	74LVC823A v.3
Modifications:	<ul style="list-style-type: none"> • Features corrected (errata). 			
74LVC823A v.3	20130327	Product data sheet	-	74LVC823A v.2
Modifications:	<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 4, Table 5, Table 6, Table 7, Table 8 and Table 9: values added for lower voltage ranges. 			
74LVC823A v.2	20040510	Product specification	-	74LVC823A v.1
74LVC823A v.1	19980924	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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